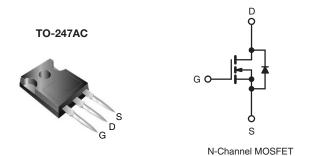


Power MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	600			
R _{DS(on)} (Ω)	V _{GS} = 10 V 0.24			
Q _g (Max.) (nC)	150			
Q _{gs} (nC)	45			
Q _{gd} (nC)	76			
Configuration	Sing	Single		



FEATURES

ullet Low Gate Charge Q_g Results in Simple Drive Requirement



 Improved Gate, Avalanche and Dynamic dV/dt RoHS Ruggedness

- Fully Characterized Capacitance and Avalanche Voltage and Current
- Enhanced Body Diode dV/dt Capability
- Compliant to RoHS Directive 2002/95/EC

BENEFITS

- Hard Switching Primary or PFS Switch
- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply
- High Speed Power Switching
- Motor Drive

ORDERING INFORMATION	
Package	TO-247AC
Lead (Pb)-free	IRFP22N60KPbF
Leau (FD)-liee	SiHFP22N60K-E3
SnPb	IRFP22N60K
	SiHFP22N60K

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V_{DS}	600	V
Gate-Source Voltage			V_{GS}	± 30] v
Continuous Drain Current	V _{GS} at 10 V	T _C = 25 °C	ı	22	
Continuous Drain Current	V _{GS} at 10 V	T _C = 100 °C	I _D	14	Α
Pulsed Drain Current ^a			I _{DM}	88	
Linear Derating Factor				2.9	W/°C
Single Pulse Avalanche Energy ^b			E _{AS}	380	mJ
Repetitive Avalanche Current ^a			I _{AR}	22	Α
Repetitive Avalanche Energy ^a			E _{AR}	37	mJ
Maximum Power Dissipation $T_C = 25 ^{\circ}C$			P _D	370	W
Peak Diode Recovery dV/dt ^c			dV/dt	15	V/ns
Operating Junction and Storage Temperature Range			T _J , T _{stg}	- 55 to + 150	°C
Soldering Recommendations (Peak Temperature)	for	10 s		300 ^d	

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. Starting T_J = 25 °C, L = 1.5 mH, R_g = 25 Ω , I_{AS} = 22 A (see fig. 12).
- c. $I_{SD} \leq 22$ A, $dI/dt \leq 360$ A/µs, $V_{DD} \leq V_{DS},$ $T_{J} \leq 150$ °C.
- d. 1.6 mm from case.

^{*} Pb containing terminations are not RoHS compliant, exemptions may apply

IRFP22N60K, SiHFP22N60K

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THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R _{thJA}	-	40	
Case-to-Sink, Flat, Greased Surface	R _{thCS}	0.24	-	°C/W
Maximum Junction-to-Case (Drain)	R _{thJC}	-	0.34	

SPECIFICATIONS (T _J = 25 °C, u					1	ı	
PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V_{DS}	V _{GS} :	= 0 V, I _D = 250 μA	600	-	-	V
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	Referenc	e to 25 °C, I _D = 1 mA ^d	-	0.30	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	V _{DS} =	$= V_{GS}, I_D = 250 \mu A$	3.0	-	5.0	V
Gate-Source Leakage	I_{GSS}		$V_{GS} = \pm 30 \text{ V}$	-	-	± 100	nA
Zero Gate Voltage Drain Current	lpaa	V _{DS} =	= 600 V, V _{GS} = 0 V	-	-	50	μΑ
Zero date voltage Brain Gunent	I _{DSS}	V _{DS} = 480 \	/, V _{GS} = 0 V, T _J = 125 °C	-	-	250	μΛ
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 13 A ^b	-	0.240	0.280	Ω
Forward Transconductance	9 fs	V _{DS}	$= 50 \text{ V}, I_D = 13 \text{ A}^b$	11	-	=	S
Dynamic							
Input Capacitance	C _{iss}		V _{GS} = 0 V,	-	3570	-	
Output Capacitance	C _{oss}]	$V_{DS} = 25 V$,	-	350	-	1
Reverse Transfer Capacitance	C _{rss}	f = 1.0 MHz, see fig. 5		-	36	-	
Output Conscitance			V _{DS} = 1.0 V , f = 1.0 MHz	-	4710	-	pF
Output Capacitance	C_{oss}	$V_{GS} = 0 V$	V _{DS} = 480 V , f = 1.0 MHz	-	92	-	
Effective Output Capacitance	C _{oss} eff.]	V _{DS} = 0 V to 480 V	-	180	-	
Total Gate Charge	Qg			-	-	150	
Gate-Source Charge	Q _{gs}	V _{GS} = 10 V	$V = I_D = 22 \text{ A}, V_{DS} = 480 \text{ V}$ see fig. 6 and 13 ^b	-	-	45	nC
Gate-Drain Charge	$Q_{\sf gd}$		ground to	-	-	76	
Turn-On Delay Time	t _{d(on)}			-	26	-	
Rise Time	t _r		$V_{DD} = 300 \text{ V}, I_D = 22 \text{ A},$		99	-] _
Turn-Off Delay Time	t _{d(off)}	$R_g =$	= 6.2, V _{GS} = 10 V, see fig. 10 ^b	-	48	-	ns -
Fall Time	t _f		g. 10	-	37	-	
Drain-Source Body Diode Characteristic	es						
Continuous Source-Drain Diode Current	Is	MOSFET sym		-	ı	22	A
Pulsed Diode Forward Current ^a	I _{SM}	integral revers p - n junction		-	-	88	A
Body Diode Voltage	V _{SD}	T _J = 25 °C	C , $I_S = 22 A$, $V_{GS} = 0 V^b$	-	-	1.5	V
Bud Birds Brown Brown Time		T _J = 25 °C		-	590	890	
Body Diode Reverse Recovery Time	t _{rr}	T _J = 125 °C		-	670	1010	ns
		T _J = 25 °C	dl/dt = 100 A/μs ^b	-	7.2	11	
Body Diode Reverse Recovery Charge	Q_{rr}			-	8.5	13	μC
Reverse Recovery Current	I _{RRM}	T _J = 25 °C		-	26	39	
Forward Turn-On Time ton Intrinsic turn-on time is negligible (turn-on is dominated by L _S and L _D)							

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. Pulse width $\leq 300~\mu s;$ duty cycle $\leq 2~\%.$
- c. C_{oss} eff. is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DS} .

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

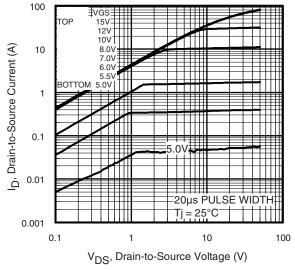


Fig. 1 - Typical Output Characteristics

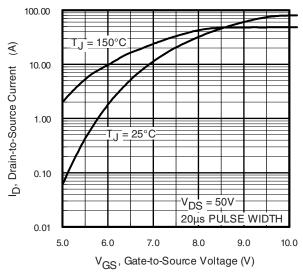


Fig. 3 - Typical Transfer Characteristics

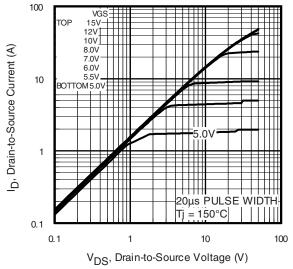


Fig. 2 - Typical Output Characteristics

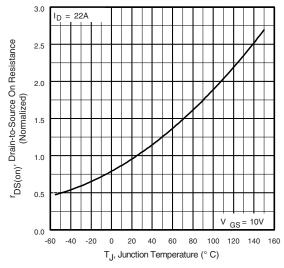


Fig. 4 - Normalized On-Resistance vs. Temperature



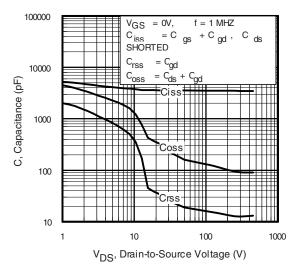


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

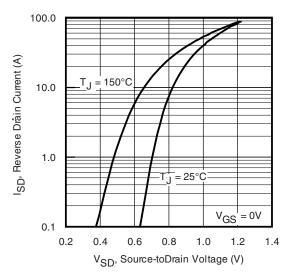


Fig. 7 - Typical Source-Drain Diode Forward Voltage

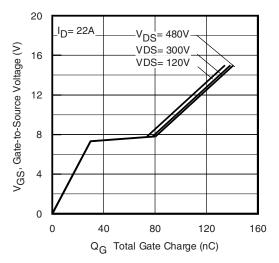


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

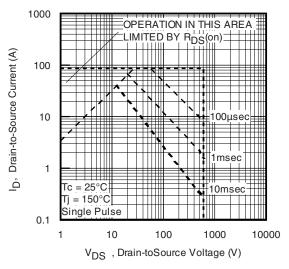
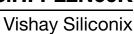


Fig. 8 - Maximum Safe Operating Area





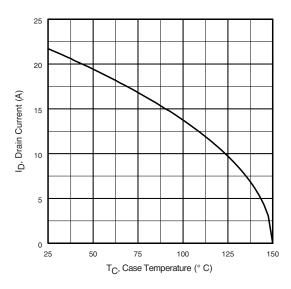


Fig. 9 - Maximum Drain Current vs. Case Temperature

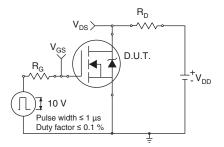


Fig. 10a - Switching Time Test Circuit

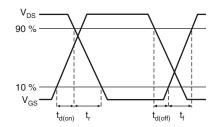


Fig. 10b - Switching Time Waveforms

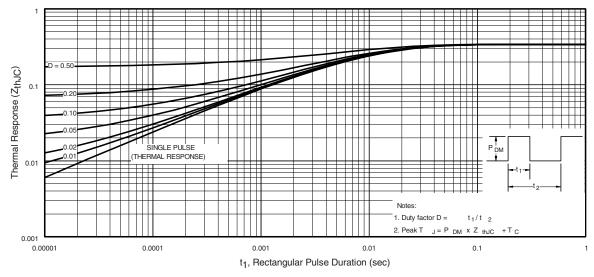
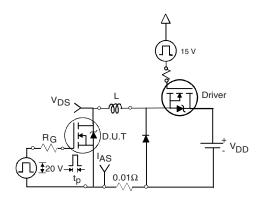


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case





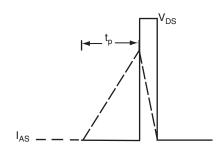


Fig. 12a - Unclamped Inductive Test Circuit

Fig. 12b - Unclamped Inductive Waveforms

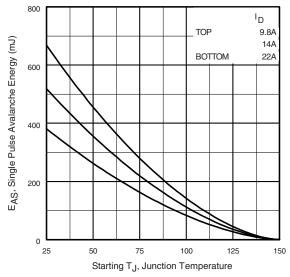


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

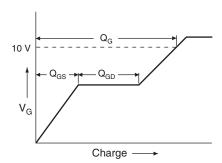


Fig. 13a - Basic Gate Charge Waveform

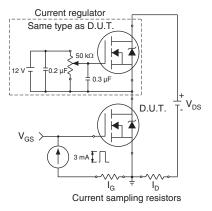
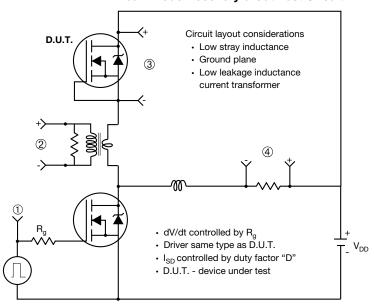


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



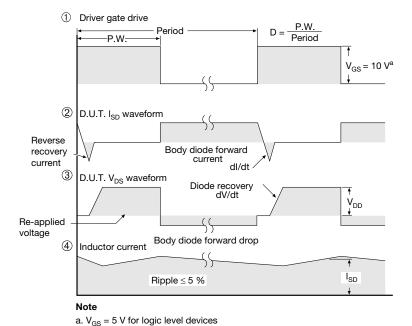


Fig. 14 - For N-Channel

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TO-247AC (High Voltage)

VERSION 1: FACILITY CODE = 9







Section C--C,D--D,E--E

	MILLIN	IETERS	
DIM.	MIN.	MAX.	NOTES
Α	4.83	5.21	
A1	2.29	2.55	
A2	1.50	2.49	
b	1.12	1.33	
b1	1.12	1.28	
b2	1.91	2.39	6
b3	1.91	2.34	
b4	2.87	3.22	6, 8
b5	2.87	3.18	
С	0.55	0.69	6
c1	0.55	0.65	
D	20.40	20.70	4

	MILLIM	MILLIMETERS	
DIM.	MIN.	MAX.	NOTES
D1	16.25	16.85	5
D2	0.56	0.76	
E	15.50	15.87	4
E1	13.46	14.16	5
E2	4.52	5.49	3
е	5.44	BSC	
L	14.90	15.40	
L1	3.96	4.16	6
ØΡ	3.56	3.65	7
Ø P1	7.19 ref.		
Q	5.31	5.69	
S	5.54	5.74	

Notes

- (1) Package reference: JEDEC® TO247, variation AC
- (2) All dimensions are in mm
- (3) Slot required, notch may be rounded
- (4) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outermost extremes of the plastic body
- (5) Thermal pad contour optional with dimensions D1 and E1
- (6) Lead finish uncontrolled in L1
- (7) Ø P to have a maximum draft angle of 1.5° to the top of the part with a maximum hole diameter of 3.91 mm
- (8) Dimension b2 and b4 does not include dambar protrusion. Allowable dambar protrusion shall be 0.1 mm total in excess of b2 and b4 dimension at maximum material condition

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VERSION 2: FACILITY CODE = Y



	MILLIMETERS		
DIM.	MIN.	MAX.	NOTES
Α	4.58	5.31	
A1	2.21	2.59	
A2	1.17	2.49	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.53	2.39	
b3	1.65	2.37	
b4	2.42	3.43	
b5	2.59	3.38	
С	0.38	0.86	
c1	0.38	0.76	
D	19.71	20.82	
D1	13.08	-	

	MILLIN		
DIM.	MIN.	MAX.	NOTES
D2	0.51	1.30	
E	15.29	15.87	
E1	13.72	-	
е	5.46	BSC	
Øk	0.2	254	
L	14.20	16.25	
L1	3.71	4.29	
ØР	3.51	3.66	
Ø P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC outline TO-247 with exception of dimension c

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VERSION 3: FACILITY CODE = N



	MILLIM	IETERS
DIM.	MIN.	MAX.
Α	4.65	5.31
A1	2.21	2.59
A2	1.17	1.37
b	0.99	1.40
b1	0.99	1.35
b2	1.65	2.39
b3	1.65	2.34
b4	2.59	3.43
b5	2.59	3.38
С	0.38	0.89
c1	0.38	0.84
D	19.71	20.70
D1	13.08	-

	MILLIMETERS		
DIM.	MIN.	MAX.	
D2	0.51	1.35	
E	15.29	15.87	
E1	13.46	-	
е	5.46	BSC	
k	0.254		
L	14.20	16.10	
L1	3.71	4.29	
N	7.62	BSC	
Р	3.56	3.66	
P1	=	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

ECN: E20-0545-Rev. F, 19-Oct-2020

DWG: 5971

Notes

- ⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")



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